



Features

- High speed□ t_{AA} = 17 ns
- Low active power □ 1073 mW (max.)
- Low CMOS standby power □ 2.75 mW (max.)
- 2.0 V data retention (400 µW at 2.0 V retention)
- Automatic power-down when deselected
- TTL-compatible inputs and outputs
- Easy memory expansion with CE and OE features

Functional Description

The CY7C1049BN is a high-performance CMOS static RAM organized as 524,288 words by 8 bits. Easy_memory expansion is provided by an_active LOW Chip Enable ($\overline{\text{CE}}$), an active LOW Output Enable ($\overline{\text{OE}}$), and three-state drivers. Writing to the device is_accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Write Enable ($\overline{\text{WE}}$) inputs LOW. Data on the eight I/O pins (I/O₀ through I/O₇) is then written into the location specified on the address pins (A_0 through A_{18}).

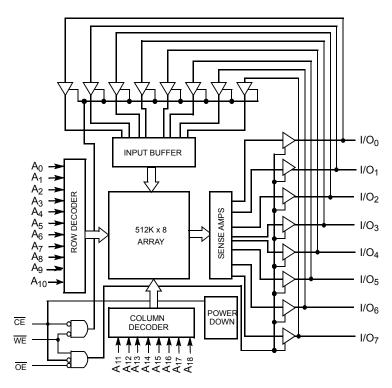
Reading from the device is accomplished by taking Chip Enable ($\overline{\text{CE}}$) and Output Enable ($\overline{\text{OE}}$) LOW while forcing Write Enable (WE) HIGH. Under these conditions, the contents of the memory location specified by the address pins will appear on the I/O pins.

The eight input/output pins (I/O $_0$ through I/O $_7$) are <u>placed</u> in a high-impedance state when the device is deselected (CE HIGH), the outputs are <u>dis</u>abled (OE HIGH), or during a write operation (CE LOW, and WE LOW).

The CY7C1049BN is available in a standard 400-mil-wide 36-pin SOJ package with center power and ground (revolutionary) pinout.

For a complete list of related documentation, click here.

Logic Block Diagram



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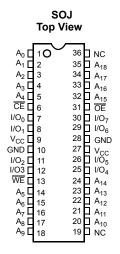
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Pinouts

Figure 1. 36-pin SOJ pinout (Top View)



Selection Guide

Description	CY7C1049BNL-17
Maximum Access Time (ns)	17
Maximum Operating Current (mA)	195
Maximum CMOS Standby Current (mA)	0.5

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Maximum Ratings

Exceeding maximum ratings may shorten the useful life of the device. These user guidelines are not tested. Storage Temperature-65 °C to +150 °C Ambient Temperature with Power Applied55 °C to +125 °C Supply Voltage on V_{CC} to Relative GND $^{[1]}$ –0.5 V to +7.0 V DC Voltage Applied to Outputs in High Z State $^{[1]}$ -0.5 V to V V

DC Input Voltage [1]	0.5 V to V _{CC} + 0.5 V
Current into Outputs (LOW)	20 mA
Static Discharge Voltage (per MIL-STD-883, Method 3015)	>2001 V
Latch-Up Current	>200 mA

Operating Range

Range	Ambient Temperature	V _{CC}
Commercial L	0 °C to +70 °C	4.5 V-5.5 V

Electrical Characteristics

Over the Operating Range

Downston	Description	Test Conditions	7C10	7C1049B-17	
Parameter			Min	Max	Unit
V _{OH}	Output HIGH Voltage	V _{CC} = Min., I _{OH} = -4.0 mA	2.4	_	V
V _{OL}	Output LOW Voltage	V _{CC} = Min., I _{OL} = 8.0 mA	_	0.4	V
V _{IH}	Input HIGH Voltage		2.2	V _{CC} + 0.3	V
V _{IL}	Input LOW Voltage [1]		-0.3	0.3	V
I _{IX}	Input Load Current	$GND \leq V_I \leq V_CC$	-1	+1	μΑ
l _{OZ}	Output Leakage Current	$\begin{aligned} &\text{GND} \leq V_{\text{OUT}} \leq V_{\text{CC}}, \\ &\text{Output Disabled} \end{aligned}$	-1	+1	μА
Icc	V _{CC} Operating Supply Current	$V_{CC} = Max.,$ $f = f_{MAX} = 1/t_{RC}$	_	195	mA
I _{SB1}	Automatic CE Power-Down Current – TTL Inputs	Max. V_{CC} , $\overline{CE} \ge V_{IH}$, $V_{IN} \ge V_{IH}$ or $V_{IN} \le V_{IL}$, $f = f_{MAX}$	-	40	mA
I _{SB2}	Automatic CE Power-Down Current – CMOS Inputs	Max. V_{CC} , $\overline{CE} \ge V_{CC} - 0.3V$, $V_{IN} \ge V_{CC} - 0.3V$ or $V_{IN} \le 0.3$ V, f = 0, Commercial	_	0.5	mA

Note
1. Minimum voltage is–2.0V for pulse durations of less than 20 ns.

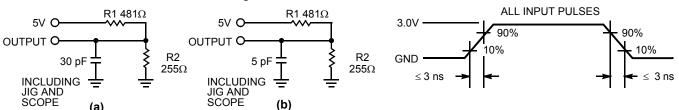


Capacitance

Parameter [2]	Description	Test Conditions	Max.	Unit
C _{IN}	Input capacitance	$T_A = 25 ^{\circ}\text{C}, f = 1 \text{MHz}, V_{CC} = 5.0 \text{V}$	8	pF
C _{OUT}	I/O capacitance		8	pF

AC Test Loads and Waveforms

Figure 2. AC Test Loads and Waveforms



Equivalent to: THÉVENIN EQUIVALENT OUTPUT O

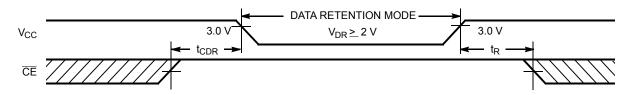
Data Retention Characteristics

Over the Operating Range

Parameter	Description		Conditions [3]	Min	Max	Unit
V_{DR}	V _{CC} for Data Retention			2.0	-	V
I _{CCDR}	Data Retention Current	Commercial L	$V_{CC} = V_{DR} = 3.0 \text{ V},$	_	200	μΑ
t _{CDR} ^[2]	Chip Deselect to Data Retention Time		$\overline{\text{CE}} \ge V_{\text{CC}} - 0.3 \text{ V},$	0	_	ns
t _R ^[4]	Operation Recovery Time		$V_{IN} \ge V_{CC} - 0.3 \text{ V or } V_{IN} \le 0.3 \text{ V}$	t _{RC}	-	ns

Data Retention Waveform

Figure 3. Data Retention Waveform



- 2. Tested initially and after any design or process changes that may affect these parameters.
- 3. No input may exceed V_{CC} + 0.5 V. 4. $t_r \le 3$ ns for the -12 and -15 speeds. $t_r \le 5$ ns for the -20 and slower speeds.



Switching Characteristics

Over the Operating Range

Parameter [5]	December 1	CY7C104	CY7C1049BNL-17	
Parameter 121	Description	Min	Max	Unit
Read Cycle				
t _{power}	V _{CC} (typical) to the First Access ^[6]	1	_	ms
t _{RC}	Read Cycle Time	17	_	ns
t _{AA}	Address to Data Valid	-	17	ns
t _{OHA}	Data Hold from Address Change	3	-	ns
t _{ACE}	CE LOW to Data Valid	-	17	ns
t _{DOE}	OE LOW to Data Valid	-	8	ns
t _{LZOE}	OE LOW to Low Z [7]	0	-	ns
t _{HZOE}	OE HIGH to High Z [7, 8]	-	7	ns
t _{LZCE}	CE LOW to Low Z [7]	3	-	ns
t _{HZCE}	CE HIGH to High Z [7, 8]	-	7	ns
t _{PU}	CE LOW to Power-Up	0	-	ns
t _{PD}	CE HIGH to Power-Down	-	17	ns
Write Cycle [9,	10]		-	
t _{WC}	Write Cycle Time	17	_	ns
t _{SCE}	CE LOW to Write End	12	-	ns
t _{AW}	Address Set-Up to Write End	12	-	ns
t _{HA}	Address Hold from Write End	0	-	ns
t _{SA}	Address Set-Up to Write Start	0	-	ns
t _{PWE}	WE Pulse Width	12	-	ns
t _{SD}	Data Set-Up to Write End	8	_	ns
t _{HD}	Data Hold from Write End	0	_	ns
t _{LZWE}	WE HIGH to Low Z [7]	3	_	ns
t _{HZWE}	WE LOW to High Z [7, 8]	-	8	ns

Notes

- Test conditions assume signal transition time of 3 ns or less, timing reference levels of 1.5V, input pulse levels of 0 to 3.0V, and output loading of the specified I_{OL}/I_{OH} and 30-pF load capacitance.
- 6. This part has a voltage regulator which steps down the voltage from 5V to 3.3V internally. t_{power} time has to be provided initially before a read/write operation is started.
- 7. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE} , t_{HZOE} is less than t_{LZOE} , and t_{HZWE} is less than t_{LZWE} for any given device.
- 8. t_{HZOE} , t_{HZCE} , and t_{HZWE} are specified with a load capacitance of 5 pF as in part (b) of AC Test Loads. Transition is measured ± 500 mV from steady-state voltage.
- 9. The internal write time of the memory is defined by the overlap of $\overline{\text{CE}}$ LOW, and $\overline{\text{WE}}$ LOW. $\overline{\text{CE}}$ and $\overline{\text{WE}}$ must be LOW to initiate a write, and the transition of either of these signals can terminate the write. The input data set-up and hold timing should be referenced to the leading edge of the signal that terminates the write.
- 10. The minimum write cycle time for Write Cycle No. 3 ($\overline{\text{WE}}$ Controlled, $\overline{\text{OE}}$ LOW) is the sum of t_{HZWE} and t_{SD} .

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Switching Waveforms

Figure 4. Read Cycle No. 1 [11, 12]

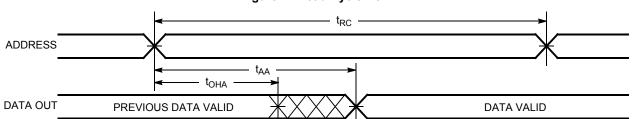
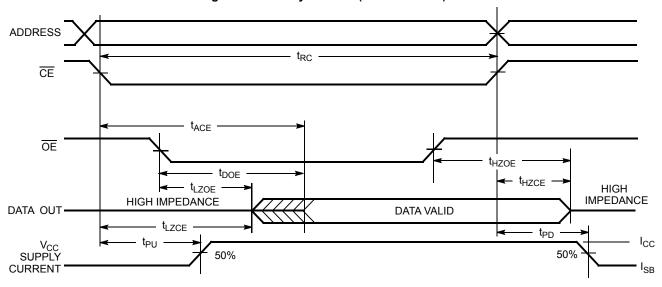


Figure 5. Read Cycle No. 2 (OE Controlled) [12, 13]



Notes

- 11. Device is continuously selected. \overline{OE} , $\overline{CE} = V_{IL}$.
- 12. $\overline{\text{WE}}$ is HIGH for read cycle.
- 13. Address valid prior to or coincident with $\overline{\text{CE}}$ transition LOW.



Switching Waveforms (continued)

Figure 6. Write Cycle No. 1 (CE Controlled) [14, 15]

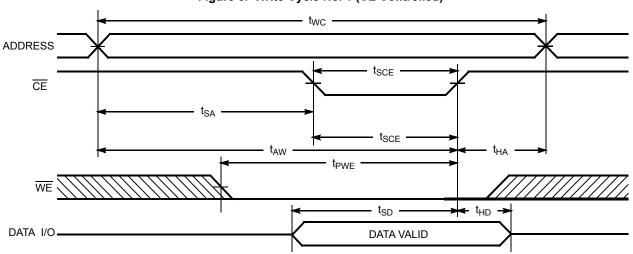
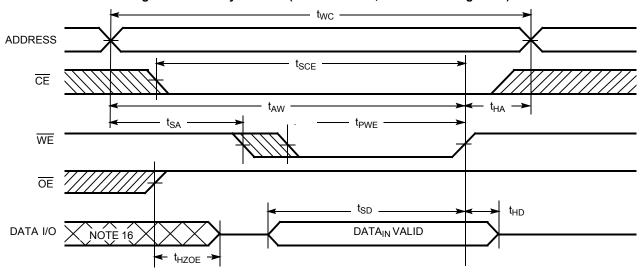


Figure 7. Write Cycle No. 2 (WE Controlled, OE HIGH during Write) [14, 15]



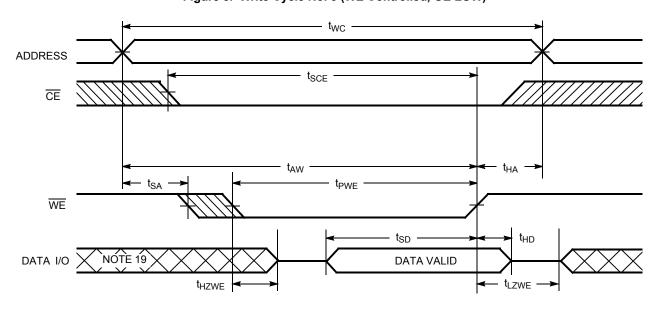
Notes

- 14. Data I/O is high impedance if $\overline{OE} = V_{IH}$.
- 15. If $\overline{\text{CE}}$ goes HIGH simultaneously with $\overline{\text{WE}}$ going HIGH, the output remains in a high-impedance state.
- 16. During this period the I/Os are in the output state and input signals should not be applied.



Switching Waveforms (continued)

Figure 8. Write Cycle No. 3 (WE Controlled, OE LOW) [17, 18]



 $[\]begin{tabular}{ll} \textbf{Notes} \\ \textbf{17. If $\overline{\sf CE}$ goes HIGH simultaneously with $\overline{\sf WE}$ going HIGH, the output remains in a high-impedance state.} \end{tabular}$

^{18.} The minimum write cycle pulse width should be equal to sum of t_{SD} and t_{HZWE} .

^{19.} During this period the I/Os are in the output state and input signals should not be applied.



Truth Table

CE	WE	OE	Inputs/Outputs	Mode	Power
Н	Х	Х	High Z	Power-down	Standby (I _{SB})
L	Н	L	Data Out	Read	Active (I _{CC})
L	L	Х	Data In	Write	Active (I _{CC})
L	Н	Н	High Z	Selected, Output disabled	Active (I _{CC})

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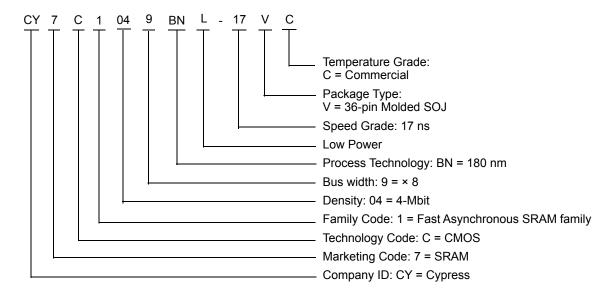
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	Speed (ns)	Ordering Code	Package Diagram	Package Type	Operating Range
Ī	17	CY7C1049BNL-17VC	51-85090	36-pin (400-Mil) Molded SOJ	Commercial

Ordering Code Definitions

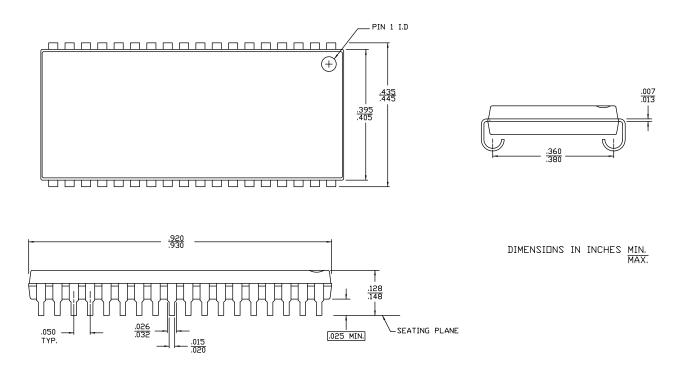


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Package Diagram

Figure 9. 36-pin SOJ V36.4 (Molded) Package Outline, 51-85090



51-85090 *G



Acronyms

Acronym	Description
CE	Chip Enable
CMOS	Complementary Metal Oxide Semiconductor
I/O	Input/Output
ŌĒ	Output Enable
SRAM	Static Random Access Memory
WE	Write Enable

Document Conventions

Units of Measure

Symbol	Unit of Measure			
°C	degree Celsius			
MHz	megahertz			
μΑ	microampere			
mA	milliampere			
mV	millivolt			
mW	milliwatt			
ns	nanosecond			
pF	picofarad			
V	volt			
W	watt			



Document History Page

Document Title: CY7C1049BN, 512 K × 8 Static RAM Document Number: 001-76449					
Revision	ECN	Orig. of Change	Submission Date	Description of Change	
**	3539227	TAVA	03/01/2012	New data sheet.	
*A	4371513	VINI	05/06/2014	Updated Switching Waveforms: Added Note 18 and referred the same note in Figure 8. Updated to new template. Completing Sunset Review.	
*B	4573121	VINI	11/18/2014	Updated Functional Description: Added "For a complete list of related documentation, click here." at the end.	
*C	4765735	VINI	05/14/2015	Updated Package Diagram: spec 51-85090 – Changed revision from *F to *G. Updated to new template. Completing Sunset Review.	
*D	6012105	AESATP12	01/03/2018	Updated logo and copyright.	

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